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	Filing Date		2004-12-24	
	First Named Inventor	YANSON et al.		
	Art Unit	2828		
	Examiner Name	Not Yet Assigned		
Attorney Docket Number		35832.000130		

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1	PAQUETTE, M. et al., "Blueshifting of InGaAsP/InP laser diodes by low-energy ion implantation", Appl. Phys. Letters 71:3749-51 (1997)	<input type="checkbox"/>
2	TAN, H. et al., "Improved intermixing in GaAs/AlGaAs quantum well structures through repeated implant-anneal sequence", presented at Conference on Optoelectronic and Microelectronic Materials and Devices Proceedings, Perth, Australia (Dec. 14 -16, 1998).	<input type="checkbox"/>
3	PAQUETTE, M. et al., "Blueshifting of InGaAsP-InP Laser Diodes Using a Low-Energy Ion-Implantation Technique: Comparison Between Strained and Lattice-Matched Quantum-Well Structures", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 4, (July/August 1998).	<input type="checkbox"/>
4	QIAN, Y., "Three-band-gap QW intermixing in InP/InGaAs/InGaAsP system for monolithically integrated optical switch", Lasers and Electro-Optics Society Annual Meeting, 1998, LEOS '98, IEEE Orlando, FL, USA, 1 - 4 Dec. 1998, Pub by IEEE Piscataway, NJ, XP010317604, pp.194-195 (Dec. 1, 1998)	<input type="checkbox"/>
5	LI, E., "Advances in intermixed quantum well devices", Electronic Devices Meeting, 1998 Proceedings, 1998 IEEE Hong Kong, Aug. 29, 1998; Pub. by IEEE Piscataway, NJ, pp.60 - 65 (1998), XP010318832.	<input type="checkbox"/>
6	UTPAL, Das et al, "Tailoring of Electron and Hole Energies in Strained GaAsP/AlGaAs quantum wells using fluorine-impurity-induced layer disordering", Appl. Phys. Letters, American Institute of Physics, New York, US, Vol. 60, No. 2, (13 Jan. 1992), pp. 210-212, XP000257167.	<input type="checkbox"/>
7	SOREL, M. et al., "Monolithic integration of InGaAs/AlGaInAs mach-zehnder interferometers using quantum well intermixing", LEOS 2003, 16th Annual Meeting of the IEEE Lasers & Electro-optics Society, Tucson, AZ, Oct. 27 - 28, 2003, Pub. by IEEE, New York, NY, Vol 1 of 2, Oct. 26, 2003, pp. 439-440, XP010676256	<input type="checkbox"/>
8	PIVA, P. et al., "Bandgap Tuning of Semiconductor Quantum Well Structures Using Ion Implantation", Superlattices and Microstructures, Academic Press, London, UK, Vol. 15, No. 4 (1994), pp. 385-389, XP000608697	<input type="checkbox"/>
9	MIYAZAWA, T. et al., "Compositional Disordering of In0.53Ga0.47As/In0.52Al0.48As Multiquantum Well Structures by Repetitive Rapid Thermal Annealing", Japanese Journal of Applied Physics 28, (May 1989) No. 5.II, Tokyo, JP	<input type="checkbox"/>
10	International Preliminary Report on Patentability, European Patent Office acting as ISA, for International Application No. PCT/GB2004/004944, dated 12 June 2006.	<input type="checkbox"/>

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